

Attorney Docket No. FUJI:294

Amendments to the Specification

Please amend the specification as follows:

Please replace paragraphs 0068 and 0069, with the following rewritten paragraph:

[0068] A CrB film 100 nm thick was deposited on a glass substrate. After patterning, the processes of drying (at 150°C) and UV treatment (at room temperature and at 150°C) were conducted to form a reflective electrode of CrB. Deposition of the CrB film was carried out by a DC sputtering method under room temperature using sputtering gas of argon supplying sputtering power of 300 W. ~~On the reflective electrode of CrB, an anode of IZO that was 125 nm thick was formed. Deposition of the anode of IZO was carried out by DC sputtering using a target of IZO (In₂O₃-10%ZnO) and argon as the sputtering gas.~~

[0069] The glass substrate with the reflective layer and the anode electrode of CrB formed thereon in the previous steps was moved to an evaporation apparatus. The vacuum chamber was evacuated to 1×10^{-5} Pa. Holding the vacuum, an organic EL layer, a buffer structure, and a cathode were sequentially formed. The organic EL layer was comprised of a hole injection layer, a hole transport layer, an organic light emissive layer, and an electron transport layer. The hole injection layer was formed by depositing copper phthalocyanine (CuPc) to a thickness of 20 nm. The hole transport layer was formed by depositing 4,4'-bis[N-(1-naphthyl)-N-phenylamino] biphenyl (α -NPD) to a thickness of 20 nm. The organic light emissive layer was formed by depositing 4,4'-bis(2,2'-diphenylvinyl) biphenyl (DPVBi) to a thickness of 40 nm. The electron transport layer was formed by depositing aluminum chelate (Alq_3) to a thickness of 20 nm.